TOSHIBA BI-DIRECTIONAL TRIODE THYRISTOR SILICON PLANAR TYPE

SM12GZ47,SM12JZ47,SM12GZ47A,SM12JZ47A

1

AC POWER CONTROL APPLICATIONS

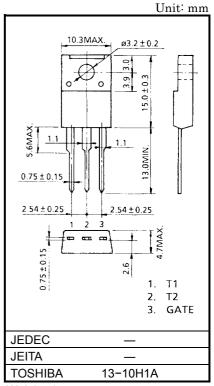
Repetitive Peak off-State Voltage : V_{DRM} = 400, 600V
 R.M.S On-State Current : I_T (RMS) = 12A

High Commutating (dv / dt)

• Isolation Voltage : $V_{Isol} = 1500V AC$

MAXIMUM RATINGS

CHARACTERI	STIC	SYMBOL	RATING	UNIT	
Repetitive Peak Off-State Voltage and	SM12GZ47 SM12GZ47A	V_{DRM}	400	V	
Repetitive Peak Reverse Voltage	SM12JZ47 SM12JZ47A	V DRM	600		
R. M. S. On-tate Currer (Full Sine Waveform TC		I _{T (RMS)}	12	Α	
Peak One Cylce Surge	On-State	I _{TSM}	120 (50Hz)	А	
Current (Non-Repetitive	e)		132 (60Hz)		
I ² t Limit Value		ı²t	72	A ² s	
Critical Rate of Rise of C Current	On-State (Note 1)	di / dt	50	A / μs	
Peak Gate Power Dissip	ation	P_{GM}	5	W	
Average Gate Power Dis	ssipation	P _{G (AV)}	0.5	W	
Peak Gate Voltage		V_{FGM}	10	V	
Peak Gate Current		I_{GM}	2	Α	
Junction Temperature		Tj	-40~125	°C	
Storage Temperature R	ange	T _{stg}	-40~125	°C	
Isolation Voltage (AC, t	= 1min.)	V _{Isol}	1500	V	



Weight: 1.7g

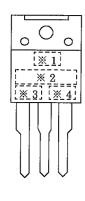
Note 1: di / dt test condition $V_{DRM} = 0.5 \times Rated$ $I_{TM} \le 17A$ $t_{gw} \ge 10\mu s$ $t_{gr} \le 250ns$ $i_{gp} = I_{GT} \times 2.0$



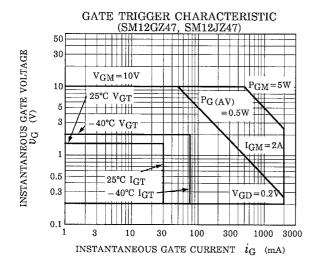
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

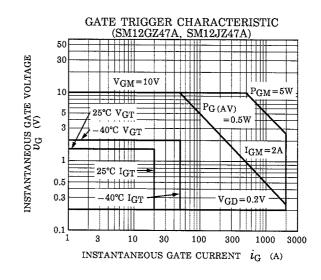
CHARACTERISTIC			SYMBOL	TEST CONDITION		MIN	TYP.	MAX	UNIT	
Repetitive Peak	Repetitive Peak Off-State Current I _{DRM} V _{DRM} = Rated			_	_	20	μA			
Gate Trigger Voltage				T2 (+) , Gate (+)	-	_	1.5			
		II	V _{GT}	$V_D = 12V$, $R_L = 20\Omega$	T2 (+) , Gate (-)	_	_	1.5	V	
		III			T2 (-) , Gate (-)	-	_	1.5		
		IV			T2 (-) , Gate (+)	-	_	_		
Gate Trigger Current SM			ı			T2 (+) , Gate (+)	-	_	30	- mA
	SM12	SM12GZ47 SM12JZ47	П			T2 (+) , Gate (-)	_	_	30	
	SM12		III			T2 (-) , Gate (-)	_	_	30	
			IV	IGT	$V_D = 12V$, $R_L = 20\Omega$	T2 (-) , Gate (+)	_	_	_	
		SM12GZ47A SM12JZ47A	I			T2 (+) , Gate (+)	_	_	20	
	SM12		П			T2 (+) , Gate (-)	_	_	20	
	SM12		III			T2 (-) , Gate (-)	_	_	20	
			IV			T2 (-) , Gate (+)	-	_	_	
Peak On-State Voltage		V _{TM}	I _{TM} = 17A		_	_	1.5	V		
Gate Non-Trigger Voltage		V_{GD}	V _D = Rated, Tc = 125°C		0.2	_	_	V		
Holding Current		lн	V _D = 12V, I _{TM} = 1A		_	_	50	mA		
Thermal Resistance		R _{th (j-c)}	Junction to Case, AC		_	_	3.0	°C/W		
Critical Rate of Rise of Off-State Voltage	SM12GZ47 SM12JZ47		dy / dt	v / dt V_{DRM} = Rated, T_j = 125°C Exponential Rise		_	300	_	- V/µs	
	SM12GZ47 SM12JZ47		uv / ut			_	200	_		
Critical Rate of Rise of Off-State	9	SM12GZ47 SM12JZ47		(dv / dt) -	V _{DRM} = 400V, T _j = 125°C		10	_	_	V / 110
Voltage at		SM12GZ47 SM12JZ47		(dv / dt) c	(di / dt) c = -6.5A / ms		4	_	_	- V/μs

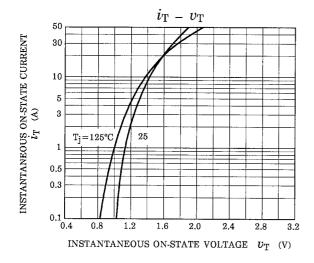
MARKING

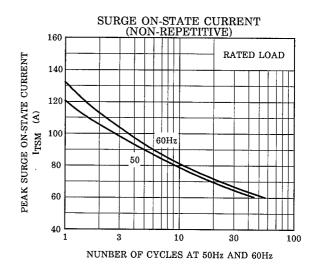


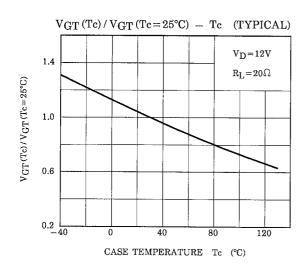
*NUMBEF		SYMBOL		
*1	TOSHIBA PRODUC	TOSHIBA PRODUCT MARK		
*2		SM12GZ47, SM12GZ47A	M12GZ47	
2	TYPE	SM12JZ47, SM12JZ47A	M12JZ47	
*3		SM12GZ47A, SM12JZ47A	Α	
*4		(Starting from Alphabet A) (Last Decimal Digit of the Current Year)	Example 8A: January 1998 8B: February 1998 8L: December 1998	

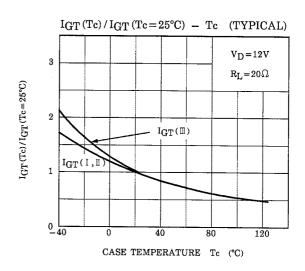


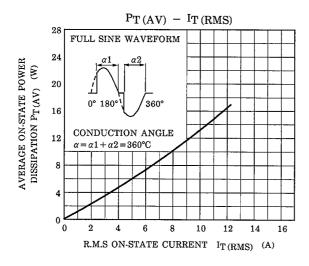


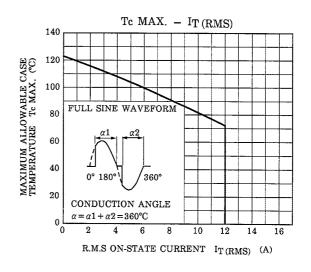


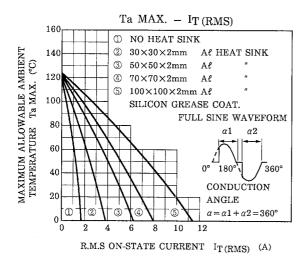


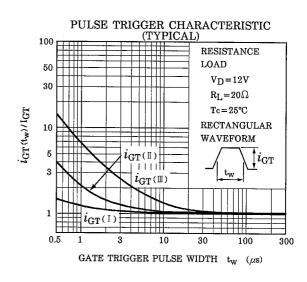


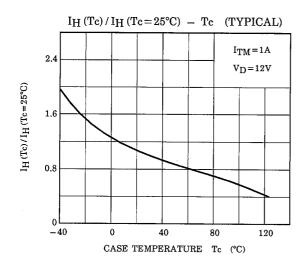


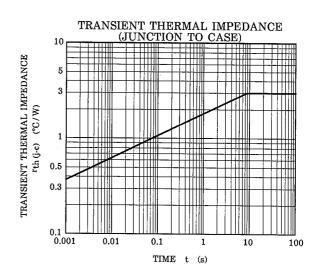












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